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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HSB88WA

Silicon Schottky Barrier Diode for High Speed Switching



ADE-208-965 (Z)

Rev.0
Aug. 2000

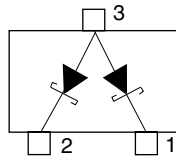
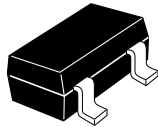
Features

- Low reverse current, Low capacitance.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSB88WA	C7	CMPAK

Pin Arrangement



(Top View)

- 1 Cathode
- 2 Cathode
- 3 Anode

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	10	V
Average rectified current	I_O^*	15	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Note: Per one device.

Electrical Characteristics

(Ta = 25°C) *¹

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_{F1}	0.350	—	0.420	V	$I_F = 1 \text{ mA}$
	V_{F2}	0.500	—	0.580		$I_F = 10 \text{ mA}$
Reverse current	I_{R1}	—	—	0.2	μA	$V_R = 2 \text{ V}$
	I_{R2}	—	—	10		$V_R = 10 \text{ V}$
Capacitance	C	—	—	0.80	pF	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$
Capacitance deviation	ΔC	—	—	0.10	pF	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$
Forward voltage deviation	ΔV_F	—	—	10	mV	$I_F = 10 \text{ mA}$
ESD-Capability * ²	—	30	—	—	V	C = 200 pF, R = 0 Ω, Both forward and reverse direction 1 pulse.

Notes: 1. Per one device.

2. Failure criterion ; $I_R > 0.4 \text{ μA}$ at $V_R = 2 \text{ V}$

Main Characteristic

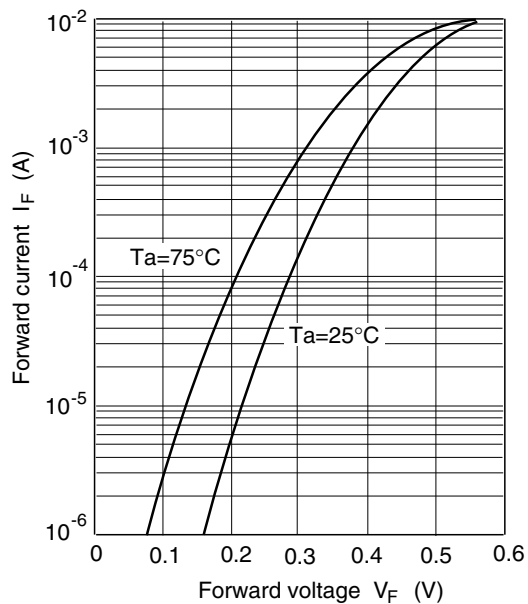


Fig.1 Forward current Vs. Forward voltage

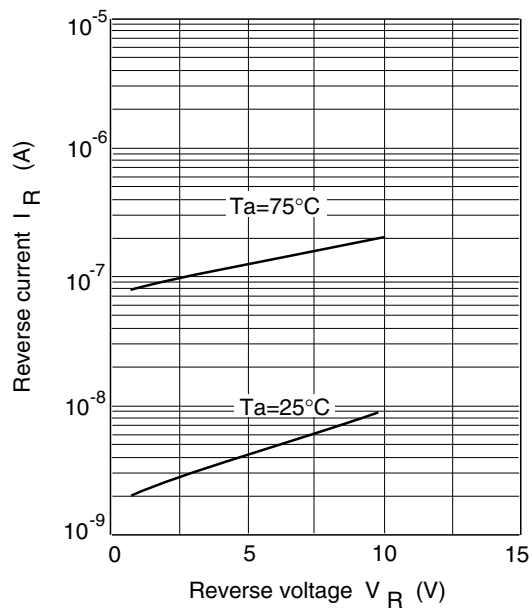


Fig.2 Reverse current Vs. Reverse voltage

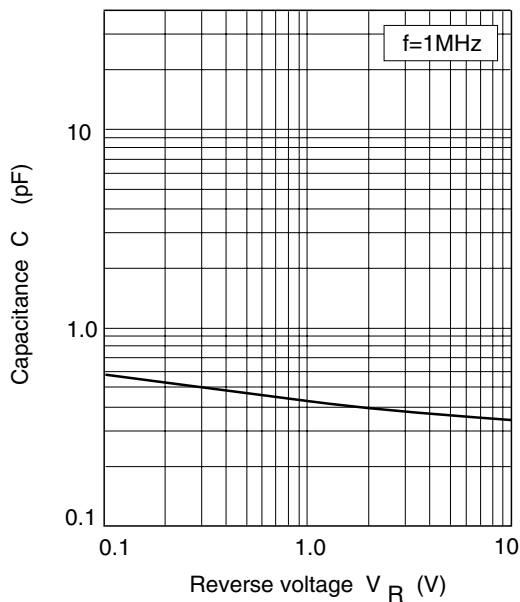
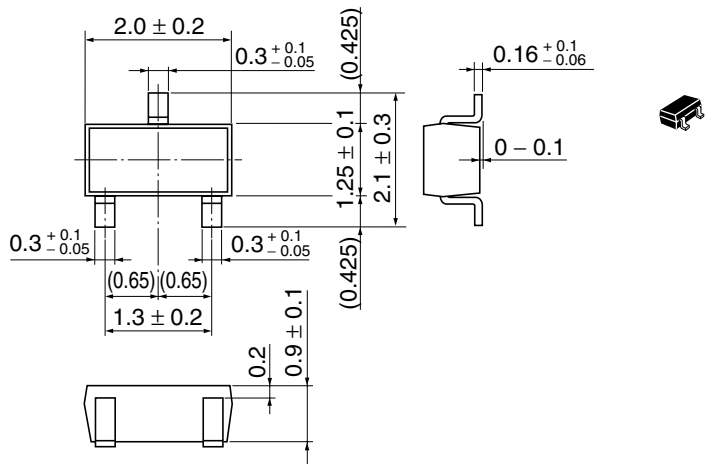


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



Hitachi Code	CMPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.006 g

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